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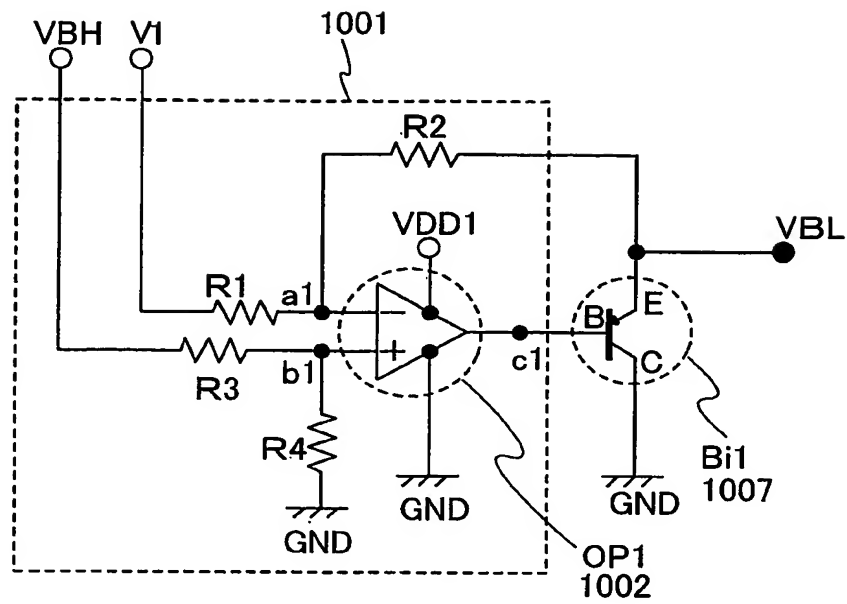
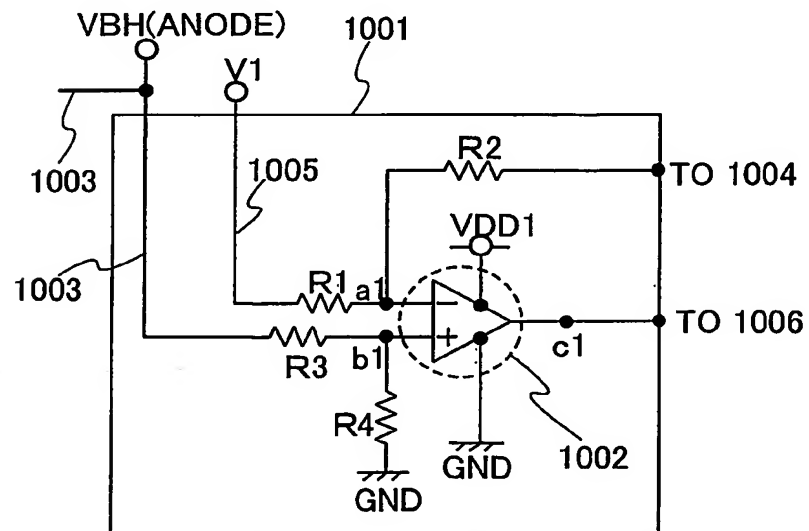
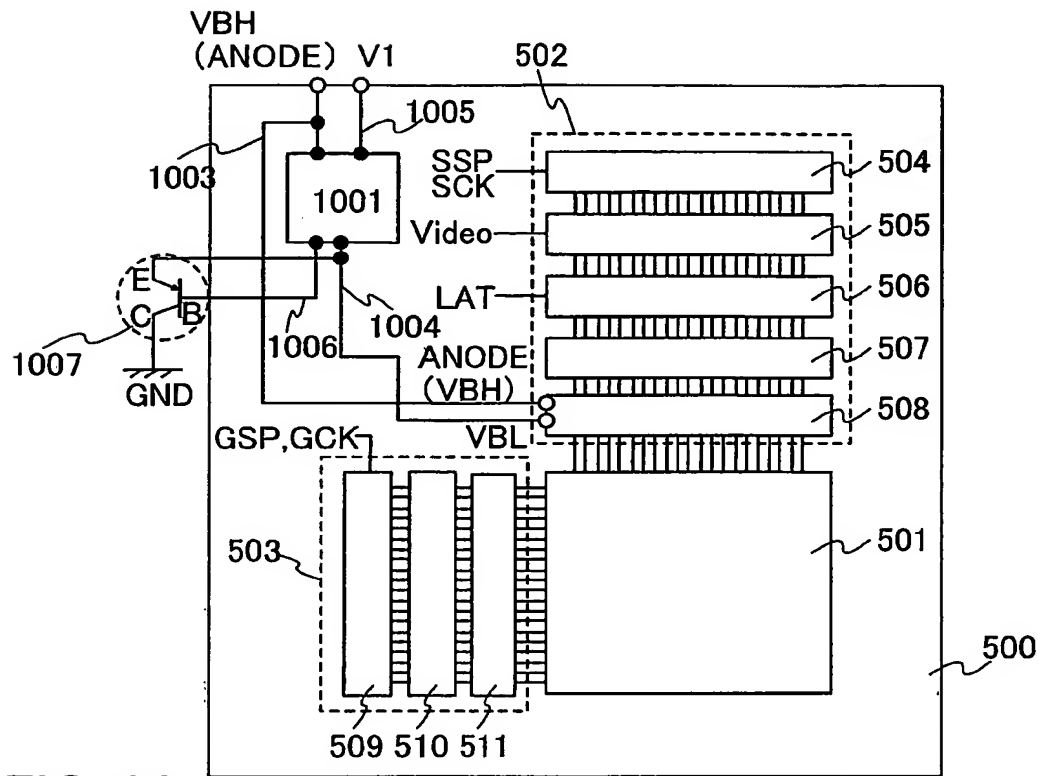


FIG. 1

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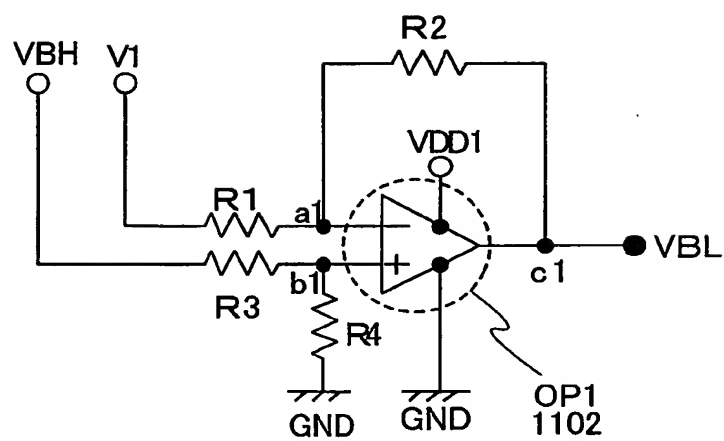


FIG. 3

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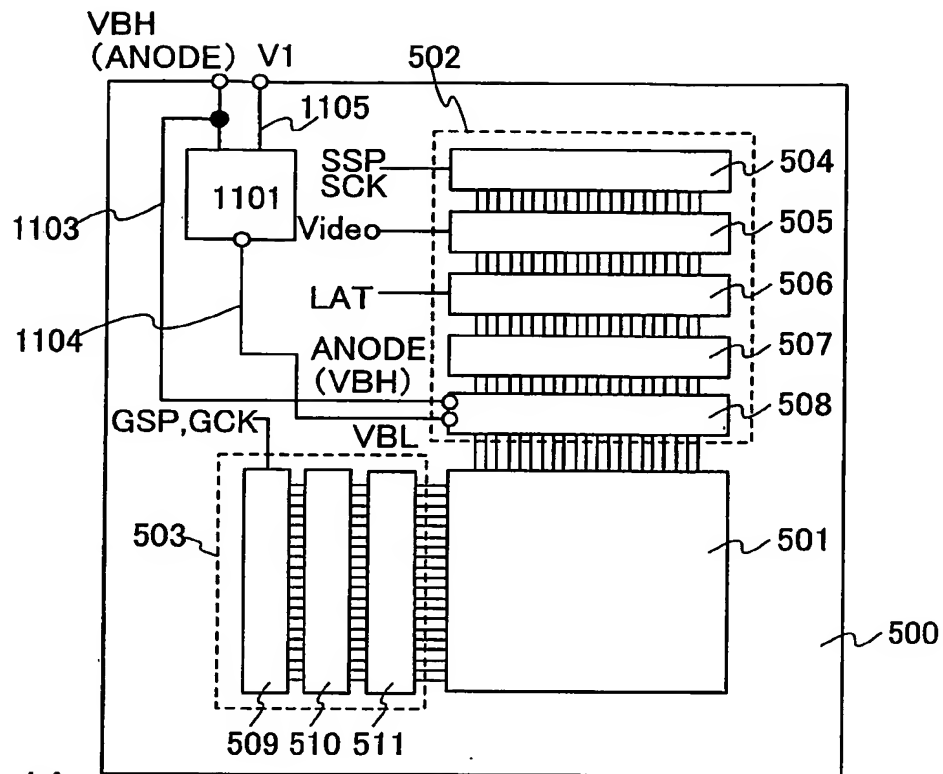


FIG. 4A

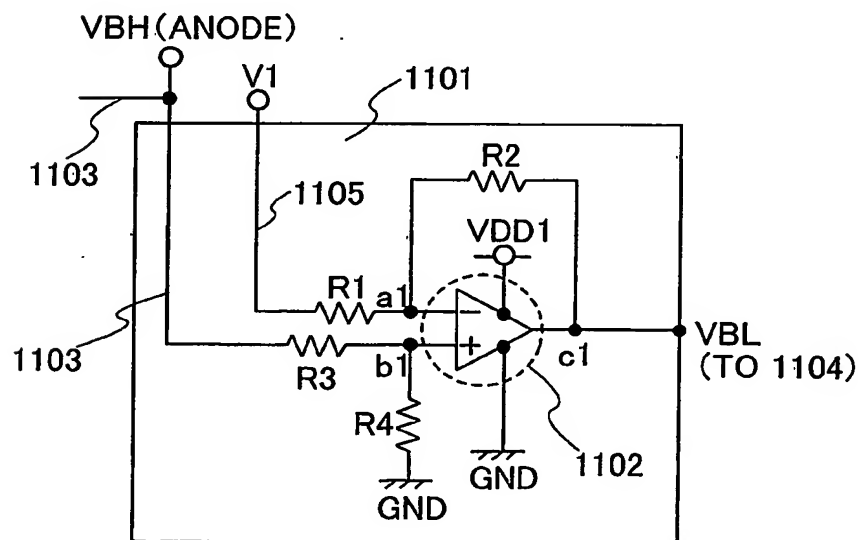


FIG. 4B

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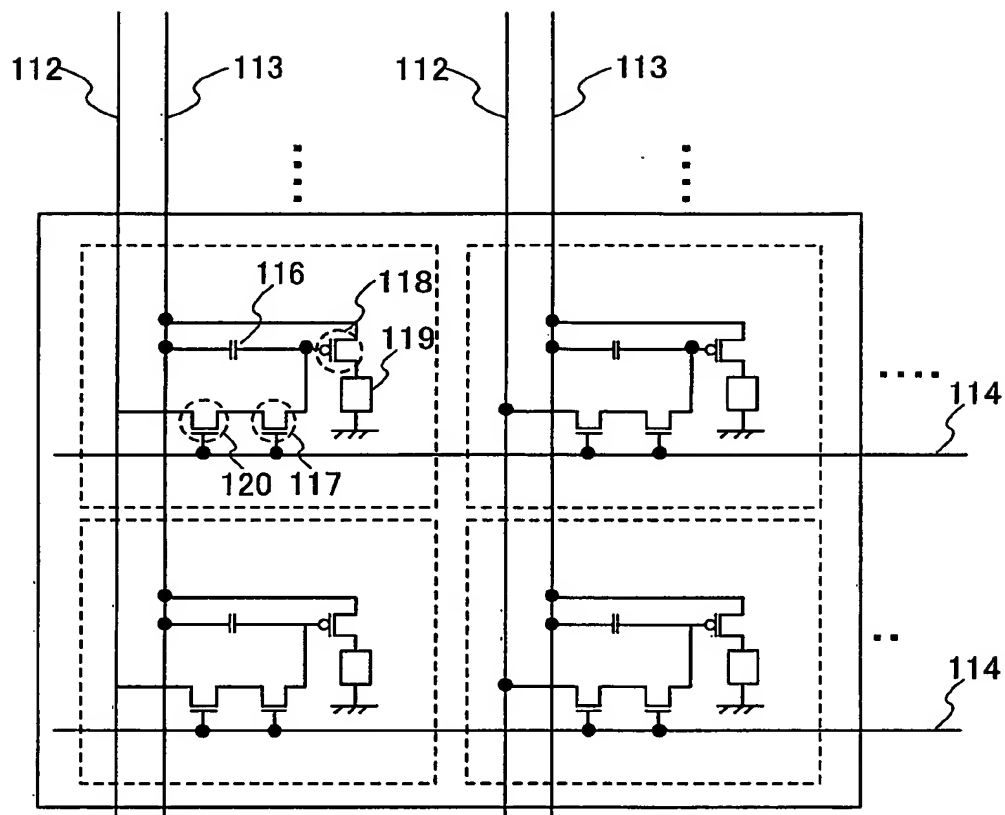


FIG. 5

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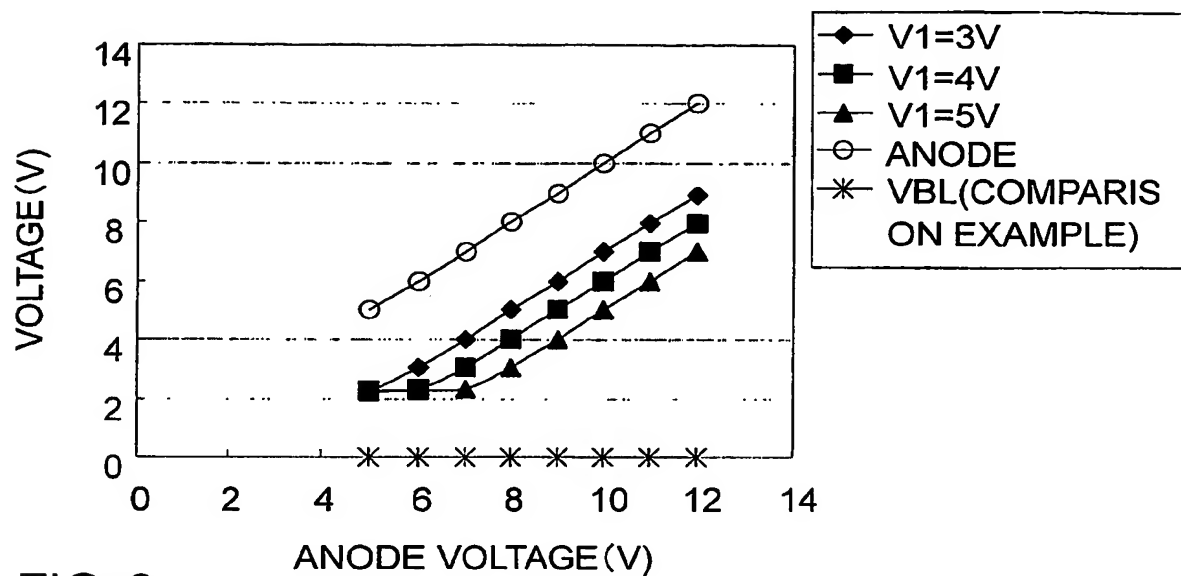


FIG. 6

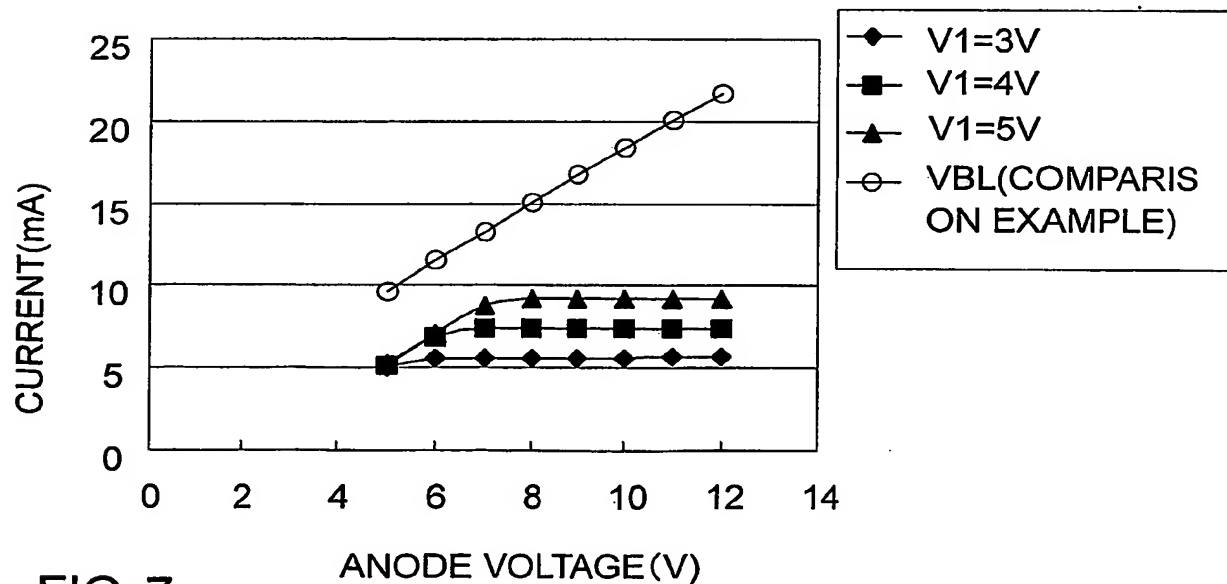


FIG. 7

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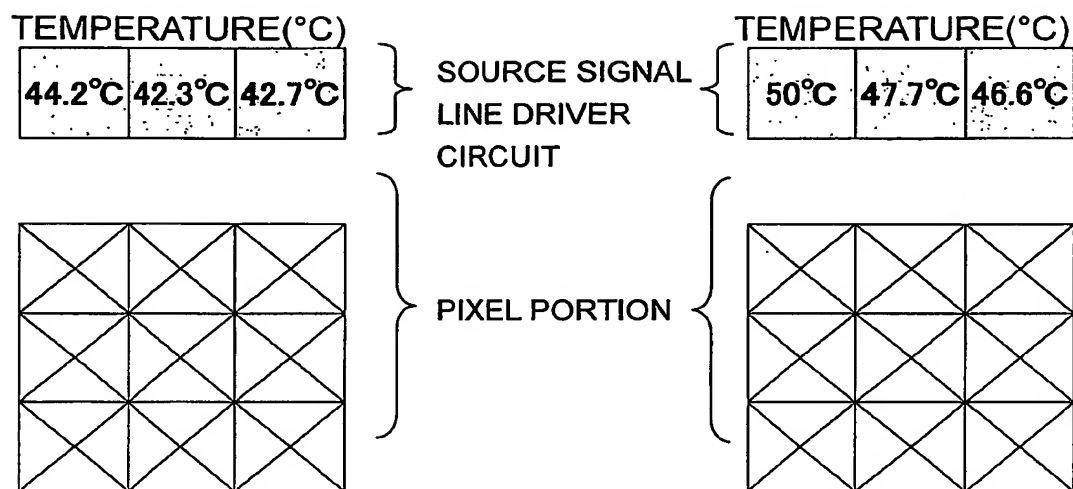


FIG. 8A

FIG. 8B

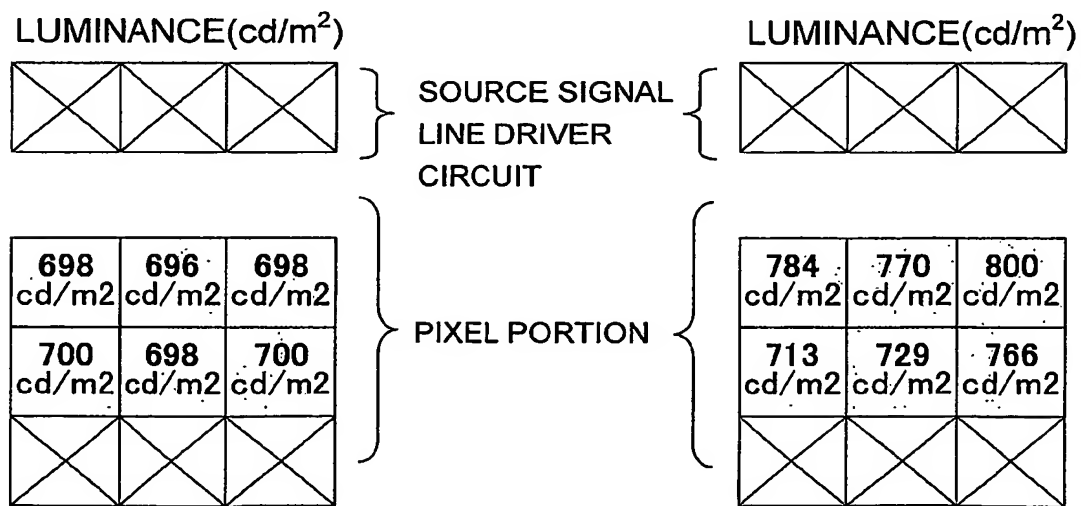


FIG. 8C

FIG. 8D

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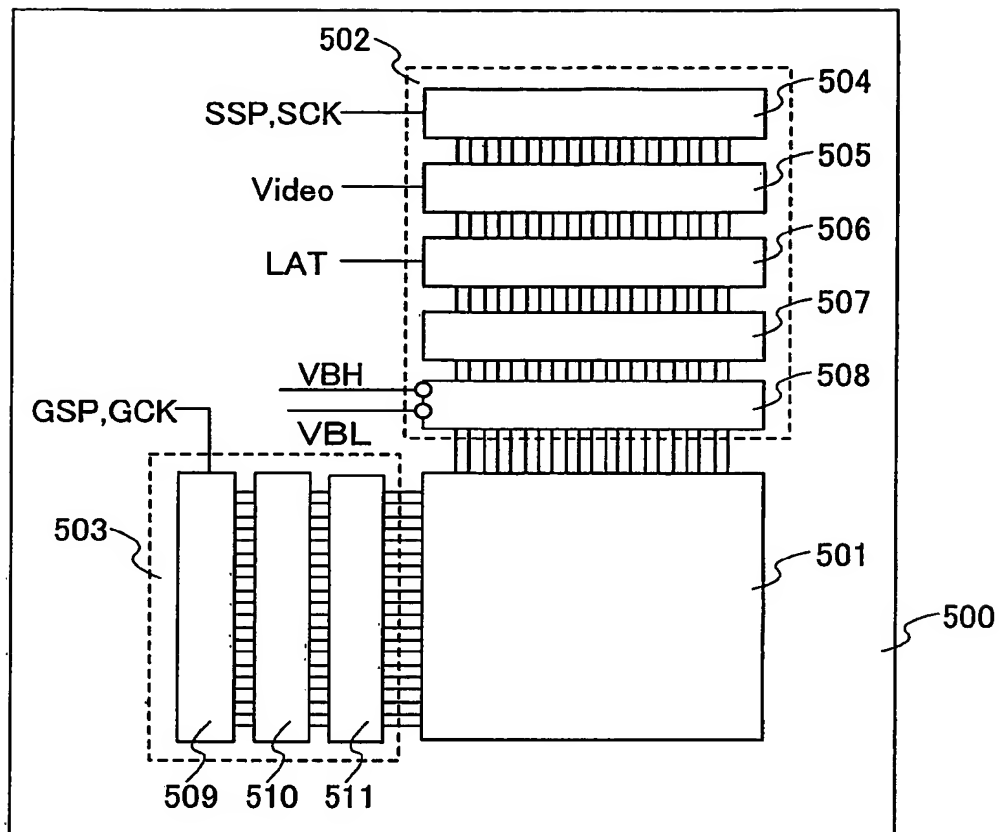


FIG. 9

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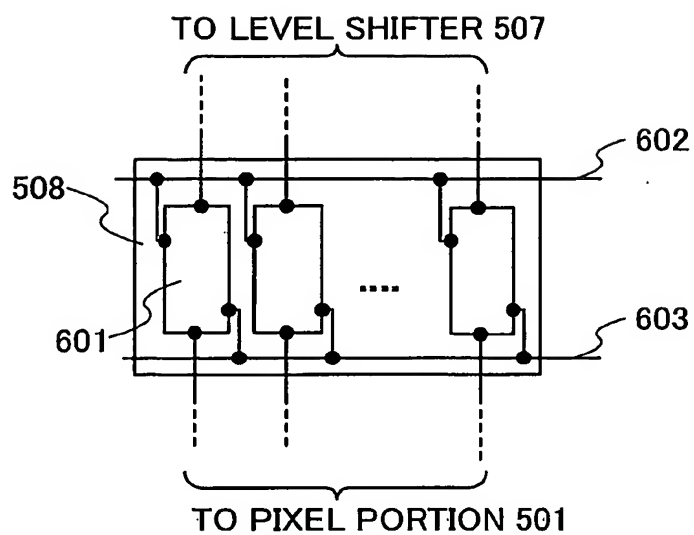


FIG. 10A

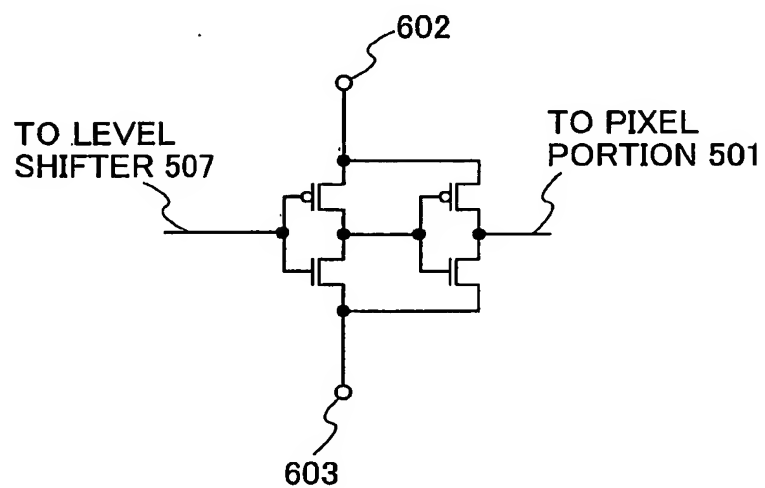


FIG. 10B

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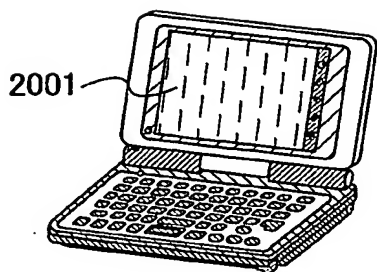


FIG. 11A



FIG. 11B

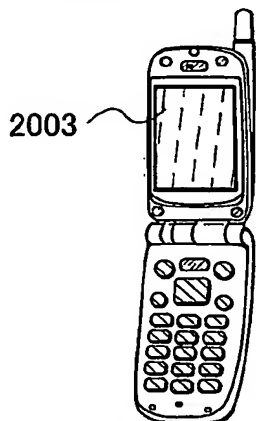


FIG. 11C

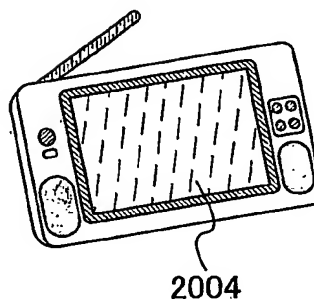


FIG. 11D

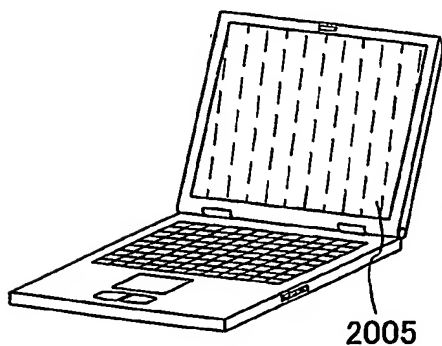


FIG. 11E

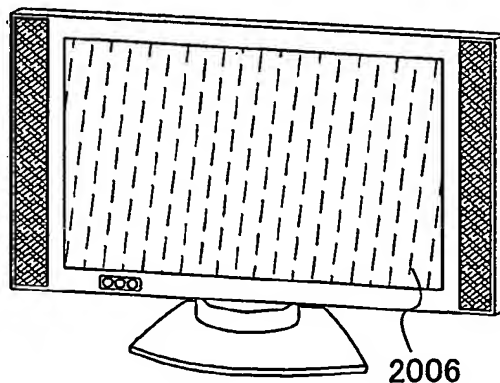


FIG. 11F

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EXPLANATION OF REFERENCE

112: source signal line, 113: signal line (power source line) which applies light emitting element high power potential (ANODE), 114: gate signal line, 116: pixel capacitor Cp, 117: n-channel TFT, 118: p-channel TFT, 119: light emitting element, 120: n-channel TFT, 500: substrate, 501: pixel portion, 502: source signal line driver circuit, 503: gate signal line driver circuit, 504: shift register, 505: first latch circuit, 506: second latch circuit, 507: level shifter, 508: buffer group circuit, 509: shift register, 510: level shifter, 511: buffer group circuit, 601: buffer, 602: signal line, 603: signal line, 1001: circuit, 1002: operational amplifier (OP1), 1003: signal line (power source line), 1004: signal line (power source line), 1005: signal line (power source line), 1007: bipolar transistor (Bi1), 1101: potential generating circuit, 1102: operational amplifier (OP1), 1103: signal line (power source line), 1104: signal line (power source line), 1105: signal line (power source line), 2001: display portion, 2002: display portion, 2003: display portion, 2004: display portion, 2005: display portion, 2006: display porton